

### N-Channel 30-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
30 V	25mΩ@10V	5.8A
	37mΩ@4.5V	

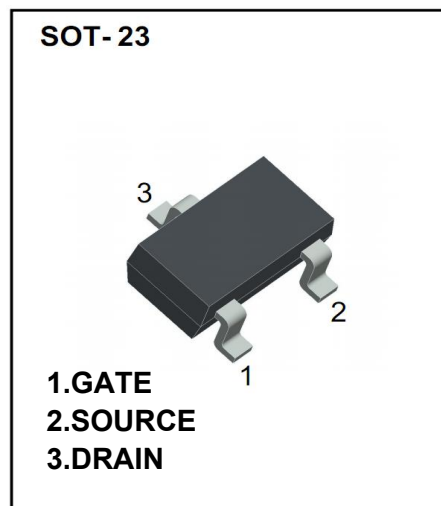
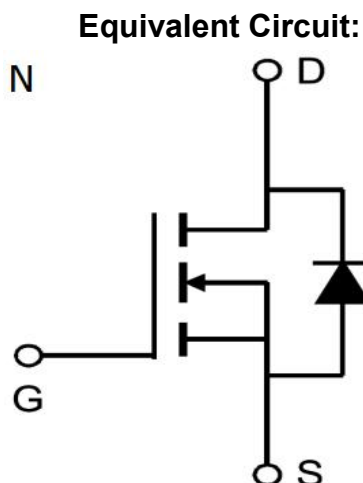
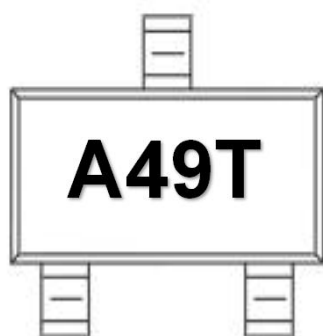
#### FEATURE:

※ TrenchFET Power MOSFET

#### DESCRIPTION :

The AO3404 use advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

#### MARKING:



#### Mosfet Maximum ratings ( Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	5.8	A
Pulsed drain current *	IDM	30	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient	RθJA	357	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C

\* Repetitive rating : Pulse width limited by maximum junction temperature.

### MOSFET ELECTRICAL CHARACTERISTICS

#### Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250μA	30			V
Gate-threshold voltage	VGS(th)	VDS = VGS, ID = 250μA	1		2.5	V
Gate-body leakage	IGSS	VDS = 0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 30V, VGS = 0V			1	μA
Drain-source on-resistancea	RDS(on)	VGS = 10V, ID = 5.8A		18	25	mΩ
		VGS = 4.5V, ID = 4.8A		27	37	mΩ
Forward transconductancea	gfs	VDS = 4.5V, ID = 5.8A		22		S
Diode forward voltage	VSD	IS = 1A, VGS = 0V		0.8	1.28	V
<b>Dynamic Parameters</b>						
Input capacitance	Ciss	VDS = 15V, VGS = 0V, f = 1MHz		373	448	pF
Output capacitance	Coss			67		pF
Reverse transfer capacitanceb	Crss			41		pF
Gate resistance	Rg	VDS = 0V, VGS = 0V, f = 1MHz		1.8	2.8	Ω
<b>Switching Parameters</b>						
Turn-on delay time	td(on)	VGS = 10V, VDS = 15V RL = 2.6Ω, RGEN = 3Ω		4.5	6.5	ns
Rise time	tr			2.4		ns
Turn-off delay time	td(off)			14.8		ns
Fall time	tf			2.5		ns
Total gate charge	Qg	VDS = 15V, VGS = 10V, ID = 5.8A		7.1	11	nC
Gate-source charge	Qgs			1.4		nC
Gate-drain charge	Qgd			1.7		nC
Body Diode Reverse Recovery Time	Trr	IF = 5.8A, dI/dt = 100A/μs		10.5		ns
Body Diode Reverse Recovery Charge	Qrr	IF = 5.8A, dI/dt = 100A/μs		4.5		nC

**Note :**

1. These parameters have no way to verify.
2. Pulse Test ; Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

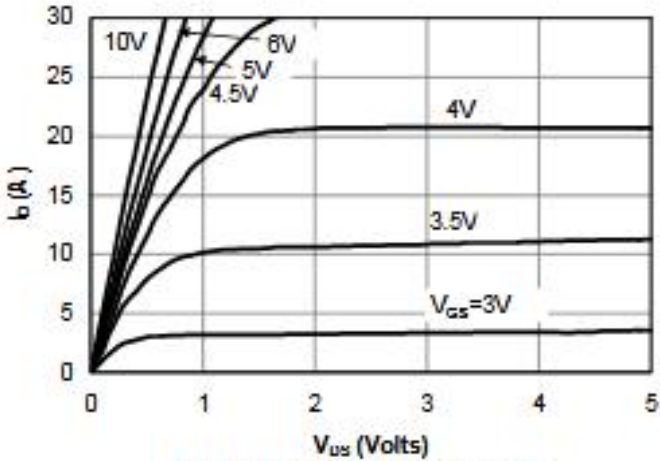


Fig 1: On-Region Characteristics

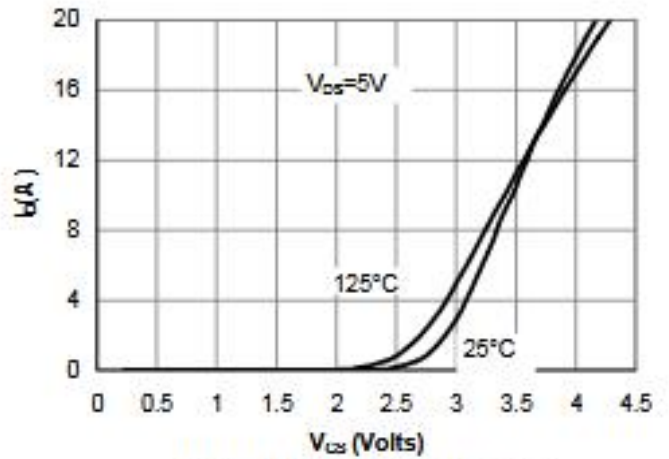


Figure 2: Transfer Characteristics

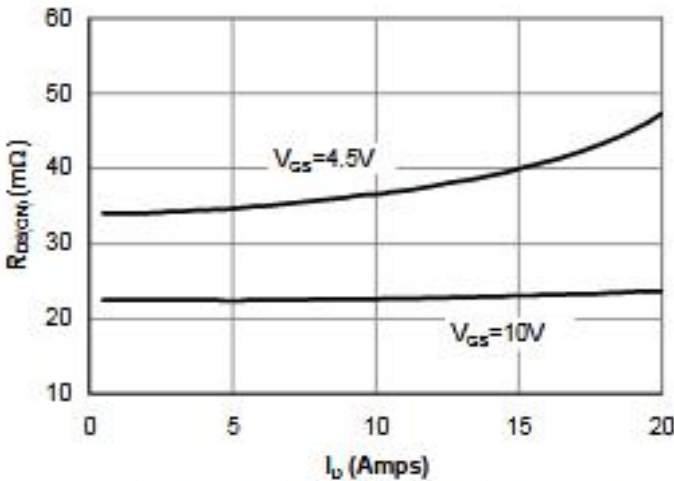


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

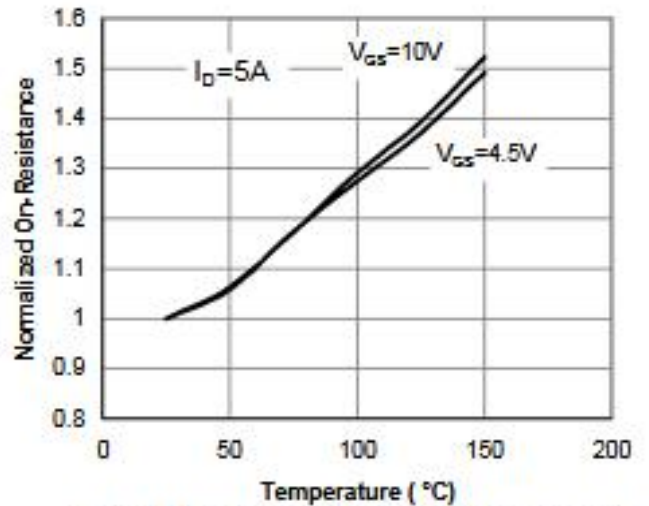


Figure 4: On-Resistance vs. Junction Temperature

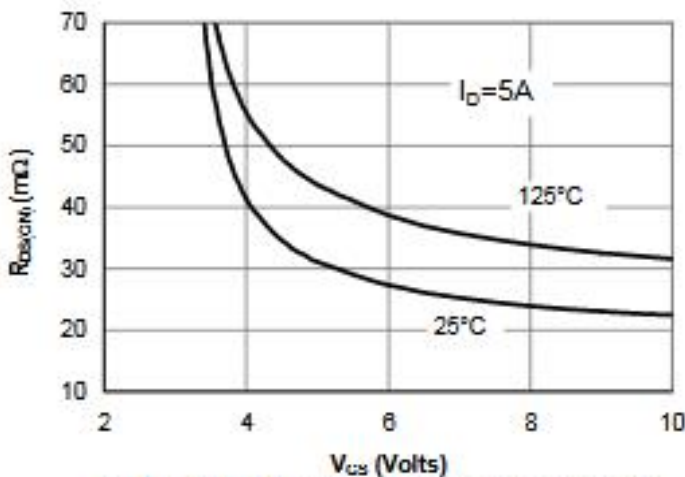


Figure 5: On-Resistance vs. Gate-Source Voltage

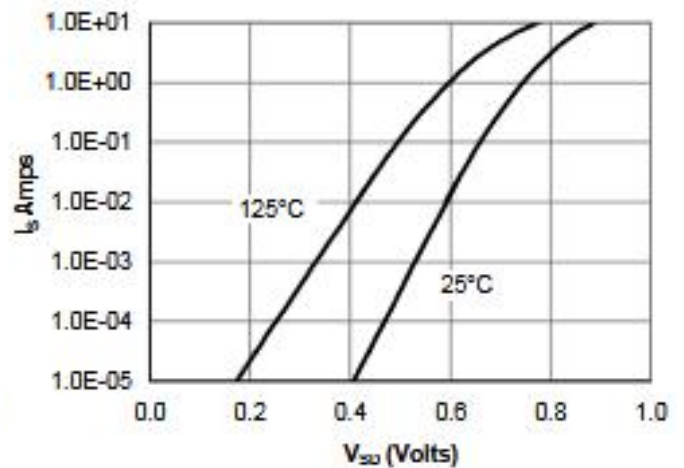


Figure 6: Body diode characteristics

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

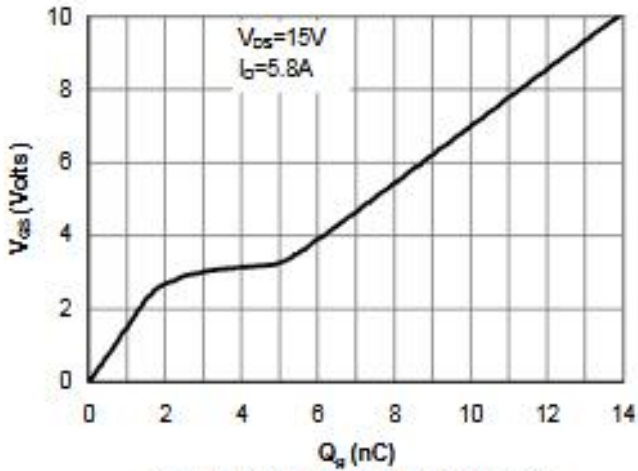


Figure 7: Gate-Charge characteristics

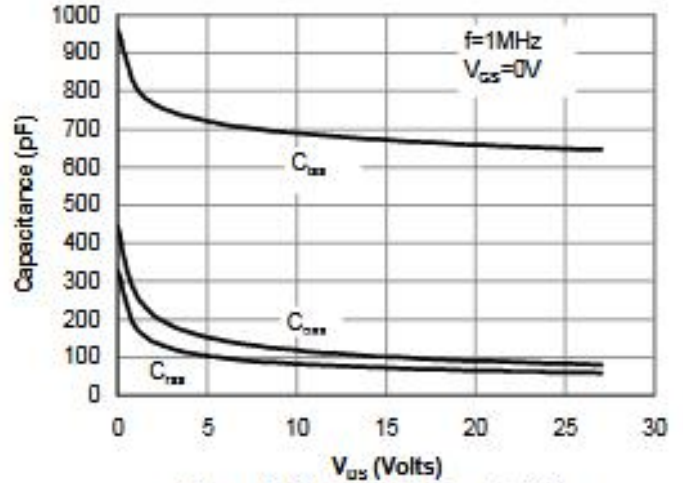


Figure 8: Capacitance Characteristics

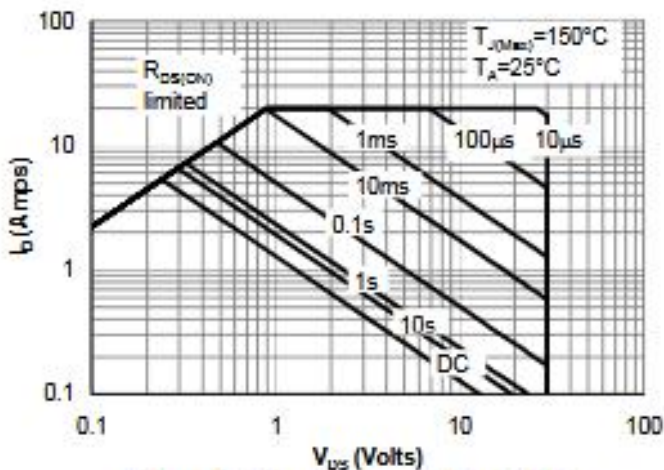


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

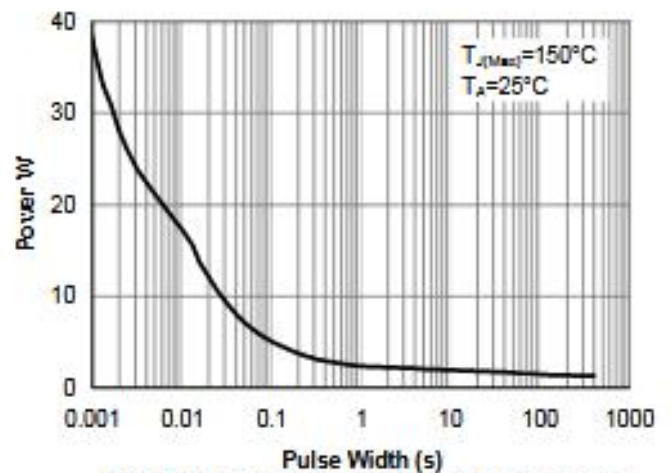


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

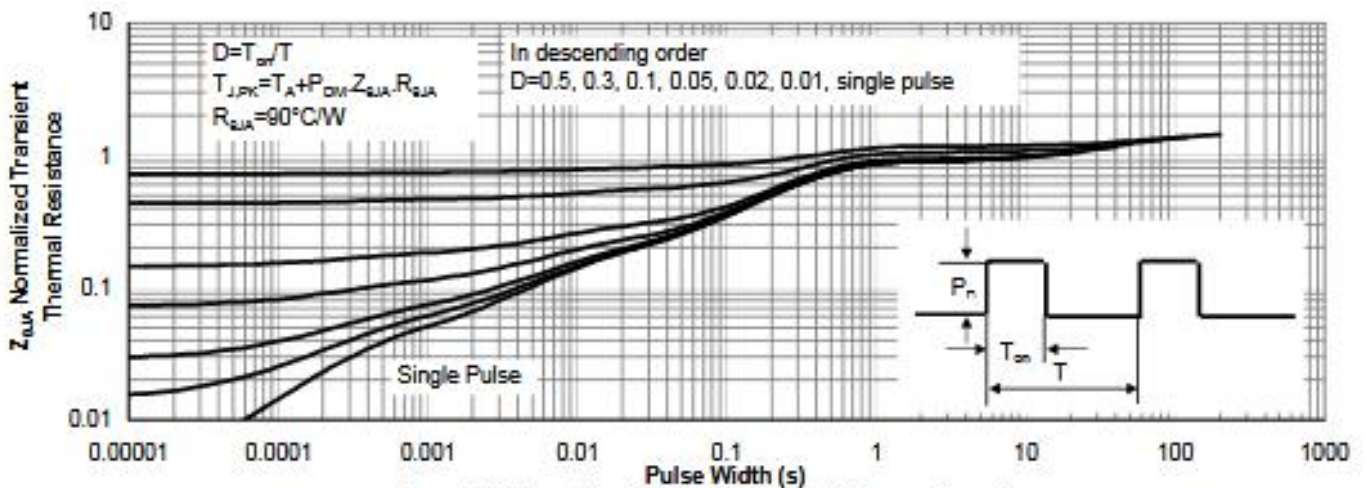
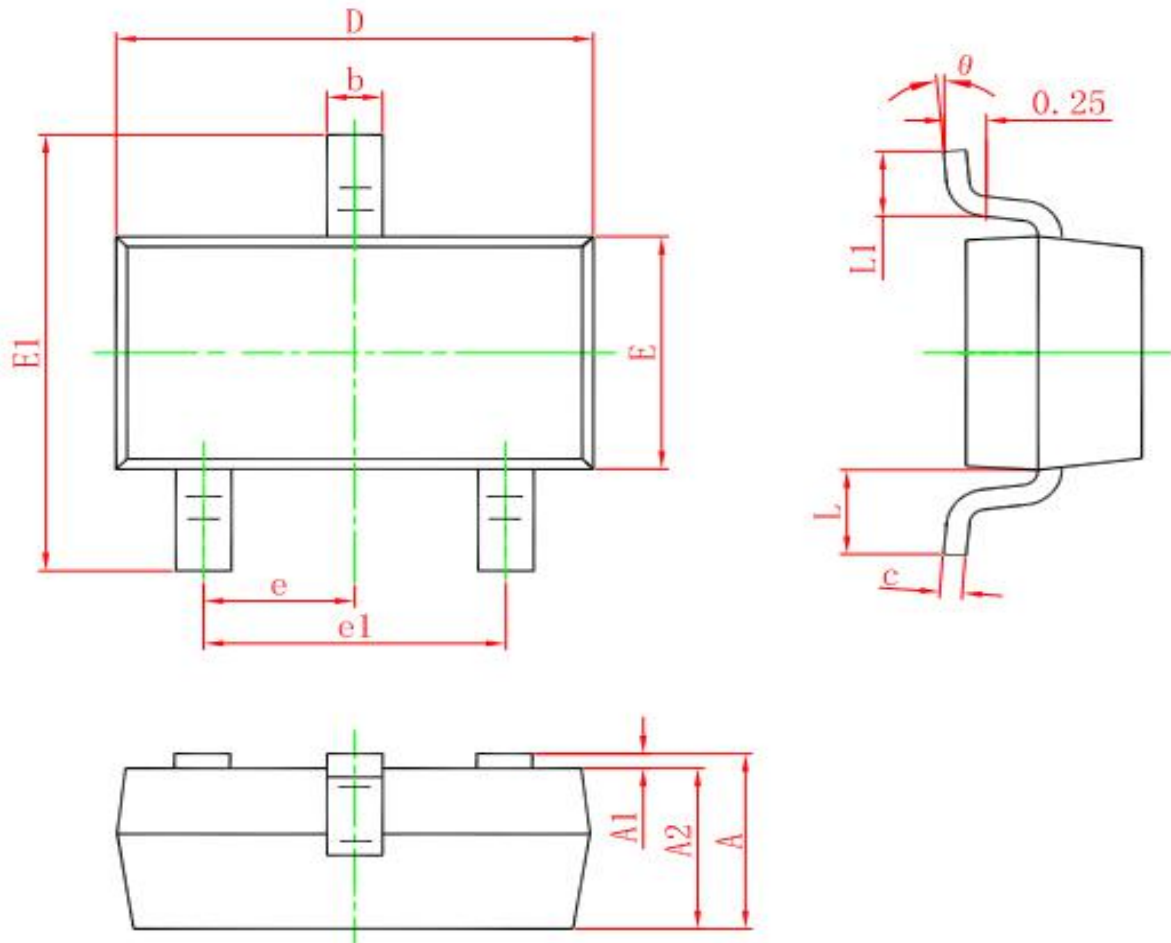


Figure 11: Normalized Maximum Transient Thermal Impedance



**SOT-23 PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Yongyutai Electronics](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)  
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#)  
[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)  
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)  
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)  
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1\\_T0\\_00201](#) [PJMF380N65E1\\_T0\\_00201](#)  
[PJMF280N60E1\\_T0\\_00201](#) [PJMF600N65E1\\_T0\\_00201](#) [PJMF900N65E1\\_T0\\_00201](#)